

# PSMN2R9-25YLC

# N-channel 25 V 3.15 m $\Omega$ logic level MOSFET in LFPAK using NextPower technology

Rev. 1 — 2 May 2011

**Product data sheet** 

### 1. Product profile

#### 1.1 General description

Logic level enhancement mode N-channel MOSFET in LFPAK package. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

#### 1.2 Features and benefits

- High reliability Power SO8 package, qualified to 175°C
- Low parasitic inductance and resistance
- Optimised for 4.5V Gate drive utilising NextPower Superjunction technology
- Ultra low QG, QGD and QOSS for high system efficiencies at low and high loads

### 1.3 Applications

- DC-to-DC converters
- Lithium-ion battery protection
- Load switching

- Power OR-ing
- Server power supplies
- Sync rectifier

#### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C	-	-	25	V
I <sub>D</sub>	drain current	$T_{mb} = 25 \text{ °C}; V_{GS} = 10 \text{ V};$ see Figure 1	<u>[1]</u> -	-	100	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>	-	-	92	W
Tj	junction temperature		-55	-	175	°C



Table 1. Quick reference data ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A};$ $T_j = 25 \text{ °C};$ see Figure 12	-	3.45	4.1	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A};$ $T_j = 25 \text{ °C};$ see Figure 12	-	2.65	3.15	mΩ
Dynamic o	characteristics					
$Q_{GD}$	gate-drain charge	$V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A};$ $V_{DS} = 12 \text{ V};$	-	4.4	-	nC
$Q_{G(tot)}$	total gate charge	see Figure 14; see Figure 15	-	16	-	nC

<sup>[1]</sup> Continuous current is limited by package.

# 2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source		
2	S	source	mb	D
3	S	source		
4	G	gate	Q	
mb	D	mounting base; connected to drain	1 2 3 4	mbb076 S
			SOT669 (LFPAK; Power-SO8)	

# 3. Ordering information

Table 3. Ordering information

Type number	Package	age				
	Name	Description	Version			
PSMN2R9-25YLC	LFPAK; Power-SO8	plastic single-ended surface-mounted package; 4 leads	SOT669			

# 4. Marking

Table 4. Marking codes

Type number	Marking code <sup>[1]</sup>
PSMN2R9-25YLC	2C925L

<sup>[1]</sup> % = placeholder for manufacturing site code.

PSMN2R9-25YLC

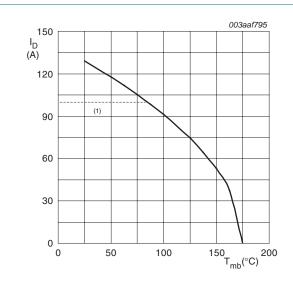
# 5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

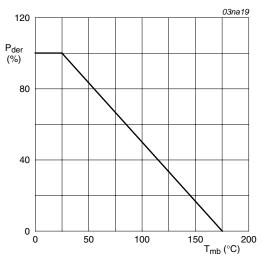
Symbol	Parameter	Conditions		Min	Max	Unit
$V_{DS}$	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C		-	25	V
$V_{DGR}$	drain-gate voltage	25 °C ≤ $T_j$ ≤ 175 °C; $R_{GS}$ = 20 kΩ		-	25	V
$V_{GS}$	gate-source voltage			-20	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; see <u>Figure 1</u>	<u>[1]</u>	-	100	Α
		V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 100 °C; see <u>Figure 1</u>		-	91	Α
I <sub>DM</sub>	peak drain current	pulsed; $t_p \le 10 \mu s$ ; $T_{mb} = 25 \text{ °C}$ ; see Figure 4		-	517	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>		-	92	W
T <sub>stg</sub>	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
T <sub>sld(M)</sub>	peak soldering temperature			-	260	°C
V <sub>ESD</sub>	electrostatic discharge voltage	MM (JEDEC JESD22-A115)		380	-	V
Source-drain	diode					
Is	source current	T <sub>mb</sub> = 25 °C		-	83	Α
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$		-	517	Α
Avalanche rug	ggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; $I_D$ = 100 A; $V_{sup} \le$ 25 V; unclamped; $R_{GS}$ = 50 $\Omega$ ; see Figure 3		-	47	mJ

<sup>[1]</sup> Continuous current is limited by package.



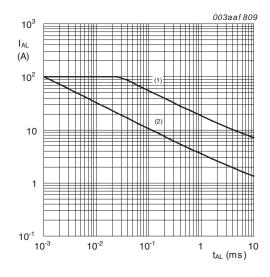
 $V_{GS} \ge 10V$ ; (1) Capped at 100A due to package

Fig 1. Continuous drain current as a function of mounting base temperature



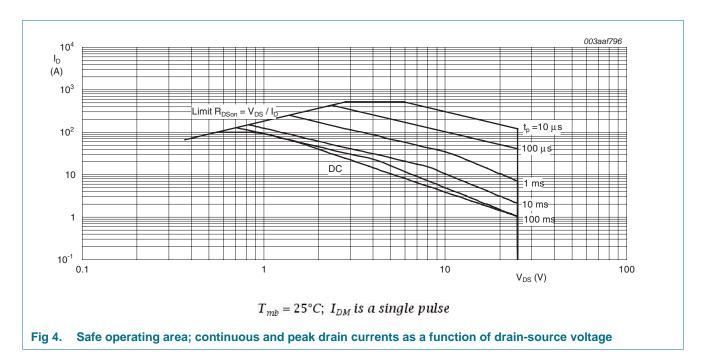
$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

Fig 2. Normalized total power dissipation as a function of mounting base temperature



(1)  $T_{j (init)} = 25^{\circ}C$ ; (2)  $T_{j (init)} = 100^{\circ}C$ 

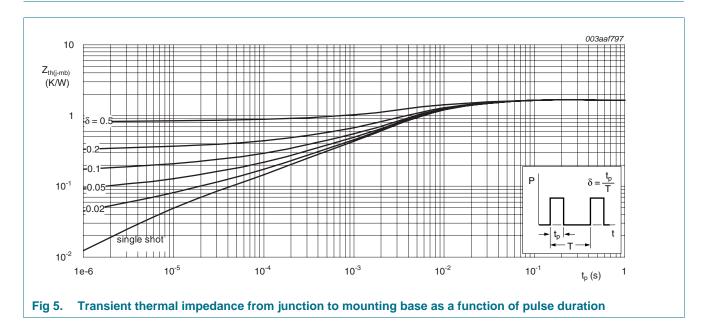
Fig 3. Single pulse avalanche rating; avalanche current as a function of avalanche time



### 6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see <u>Figure 5</u>	-	1.46	1.64	K/W



# 7. Characteristics

Table 7. Characteristics

Table 7.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
	aracteristics					
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	25	-	-	V
		$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$	22.5	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}$ ; $V_{DS} = V_{GS}$ ; $T_j = 25 \text{ °C}$ ; see <u>Figure 10</u> ; see <u>Figure 11</u>	1.05	1.54	1.95	V
		$I_D = 10 \text{ mA}; V_{DS} = V_{GS}; T_j = 150 \text{ °C}$	0.5	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C}$	-	-	2.25	V
$I_{DSS}$	drain leakage current	$V_{DS} = 25 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	1	μΑ
		$V_{DS} = 25 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 \text{ °C}$	-	-	100	μΑ
$I_{GSS}$	gate leakage current	$V_{GS} = 16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	100	nΑ
		$V_{GS} = -16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	100	nΑ
R <sub>DSon</sub> drain-source on-state resistance	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C};$ see <u>Figure 12</u>	-	3.45	4.1	mΩ
		$V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A}; T_j = 150 \text{ °C};$ see Figure 12; see Figure 13	-	-	6.6	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 ^{\circ}\text{C};$ see Figure 12	-	2.65	3.15	mΩ
		$V_{GS}$ = 10 V; $I_D$ = 25 A; $T_j$ = 150 °C; see Figure 12; see Figure 13	-	-	5.05	mΩ
$R_G$	gate resistance	f = 1 MHz	-	2	4	Ω
Dynamic	characteristics					
Q <sub>G(tot)</sub> total gate charge	total gate charge	$I_D = 25 \text{ A}$ ; $V_{DS} = 12 \text{ V}$ ; $V_{GS} = 10 \text{ V}$ ; see Figure 14; see Figure 15	-	33	-	nC
	$I_D = 25 \text{ A}$ ; $V_{DS} = 12 \text{ V}$ ; $V_{GS} = 4.5 \text{ V}$ ; see Figure 14; see Figure 15	-	16	-	nC	
		$I_D = 0 A$ ; $V_{DS} = 0 V$ ; $V_{GS} = 10 V$	-	29	-	nC
Q <sub>GS</sub>	gate-source charge	$I_D = 25 \text{ A}; V_{DS} = 12 \text{ V}; V_{GS} = 4.5 \text{ V};$	-	5	-	nC
Q <sub>GS(th)</sub>	pre-threshold gate-source charge	see <u>Figure 14</u> ; see <u>Figure 15</u>	-	3.4	-	nC
Q <sub>GS(th-pl)</sub>	post-threshold gate-source charge		-	1.6	-	nC
$Q_{GD}$	gate-drain charge		-	4.4	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 12 V; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	2.55	-	V
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 12 V; V <sub>GS</sub> = 0 V; f = 1 MHz;	-	2083	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; see <u>Figure 16</u>	-	501	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	160	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = 12 \text{ V}; R_L = 0.5 \Omega; V_{GS} = 4.5 \text{ V};$	-	19.5	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 4.7 \Omega$	-	19	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	32	-	ns
t <sub>f</sub>	fall time		-	13	-	ns
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 Table 7.
 Characteristics ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Q <sub>oss</sub>	output charge	$V_{GS} = 0 \text{ V}; V_{DS} = 12 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ °C}$	-	18.5	-	nC
Source-drain	diode					
V <sub>SD</sub>	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C};$ see <u>Figure 17</u>	-	0.8	1.1	V
t <sub>rr</sub>	reverse recovery time	$I_S = 25 \text{ A}$ ; $dI_S/dt = -100 \text{ A/}\mu\text{s}$ ; $V_{GS} = 0 \text{ V}$ ;	-	32	-	ns
Q <sub>r</sub>	recovered charge	V <sub>DS</sub> = 12 V	-	23	-	nC
t <sub>a</sub>	reverse recovery rise time	$V_{GS} = 0 \text{ V; } I_S = 25 \text{ A; } dI_S/dt = -100 \text{ A/}\mu\text{s;}$ $V_{DS} = 12 \text{ V; see } \frac{\text{Figure } 18}{\text{ Figure } 18}$	-	18	-	ns
t <sub>b</sub>	reverse recovery fall time		-	14	-	ns

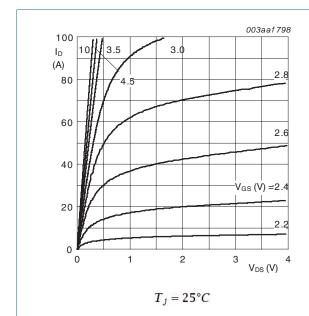
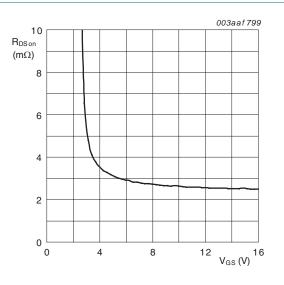


Fig 6. Output characteristics; drain current as a function of drain-source voltage; typical values



 $T_j = 25^{\circ}C; \ I_D = 25A$ 

Fig 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

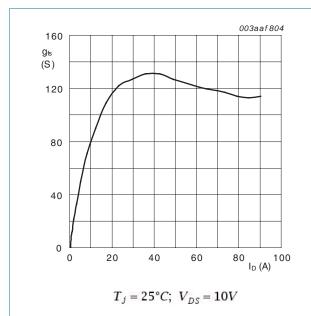


Fig 8. Forward transconductance as a function of drain current; typical values

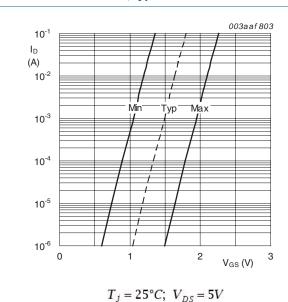


Fig 10. Sub-threshold drain current as a function of gate-source voltage

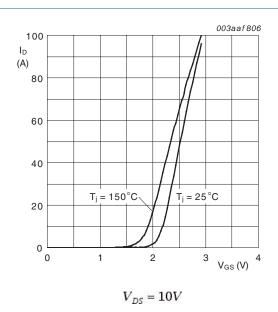


Fig 9. Transfer characteristics; drain current as a function of gate-source voltage; typical values

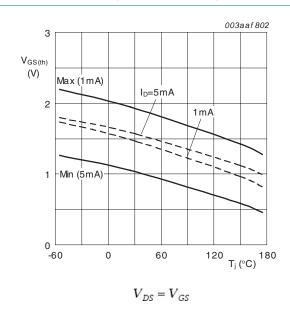


Fig 11. Gate-source threshold voltage as a function of junction temperature

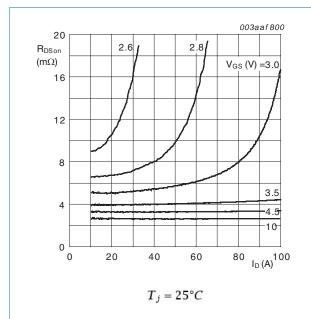


Fig 12. Drain-source on-state resistance as a function of drain current; typical values

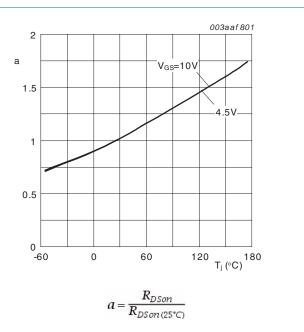


Fig 13. Normalized drain-source on-state resistance factor as a function of junction temperature

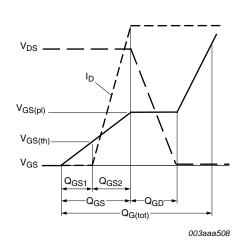


Fig 14. Gate charge waveform definitions

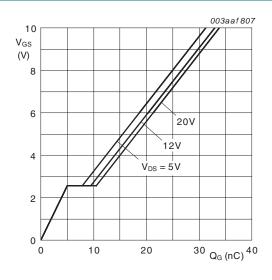


Fig 15. Gate-source voltage as a function of gate charge; typical values

 $T_j = 25^{\circ}C; \ I_D = 25A$ 

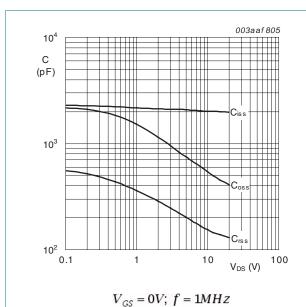


Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

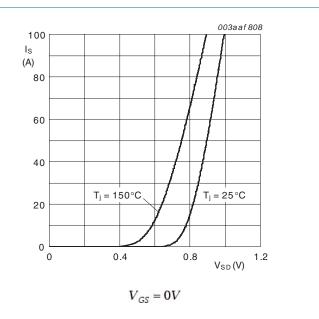


Fig 17. Source current as a function of source-drain voltage; typical values

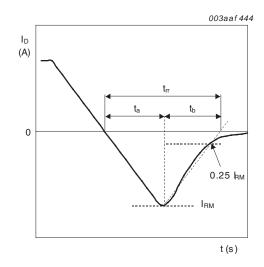


Fig 18. Reverse recovery timing definition

## 8. Package outline

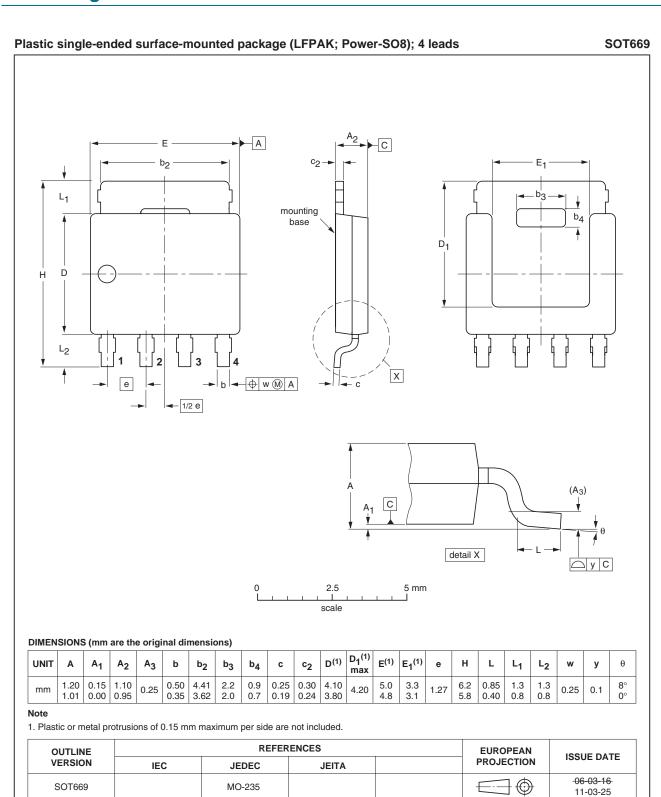


Fig 19. Package outline SOT669 (LFPAK; Power-SO8)

PSMN2R9-25YLC

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# 9. Revision history

### Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN2R9-25YLC v.1	20110502	Product data sheet	-	-

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### 10. Legal information

#### 10.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions".
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# PSMN2R9-25YLC

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For sales office addresses, please send an email to: salesaddresses@nexperia.com

## 12. Contents

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